



## APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

<b>Title of Invention</b>	METHOD OF FORMING HIGH VOLTAGE METAL OXIDE SEMICONDUCTOR TRANSISTOR		
Application Type : regular, utility Attorney Docket Number : NAUP0531USA			
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 as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			